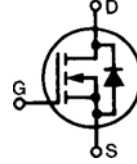


High Voltage Power MOSFETs

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt

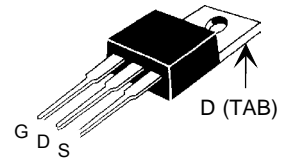
IXTA/IXTP 3N120
IXTA/IXTP 3N110

V_{DSS}	I_{D25}	$R_{DS(on)}$
1200 V	3 A	4.5 Ω
1100 V	3 A	4.0 Ω

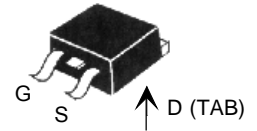


Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	3N120	1200	V
		3N110	1100	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	3N120	1200	V
		3N110	1100	V
V_{GS}	Continuous		± 20	V
V_{GSM}	Transient		± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$		3	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}		12	A
I_{AR}	$T_C = 25^\circ\text{C}$		3	A
E_{AR}	$T_C = 25^\circ\text{C}$		20	mJ
E_{AS}			700	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\infty\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$		5	V/ns
P_D	$T_C = 25^\circ\text{C}$		150	W
T_J			-55 to +150	$^\circ\text{C}$
T_{JM}			150	$^\circ\text{C}$
T_{stg}			-55 to +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (TO-220)		1.13/10	Nm/lb.in.
Weight	TO-220		4	g
	TO-263		2	g

TO-220 (IXTP)



TO-263 (IXTA)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$
- Rated for unclamped Inductive load Switching (UIS)
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

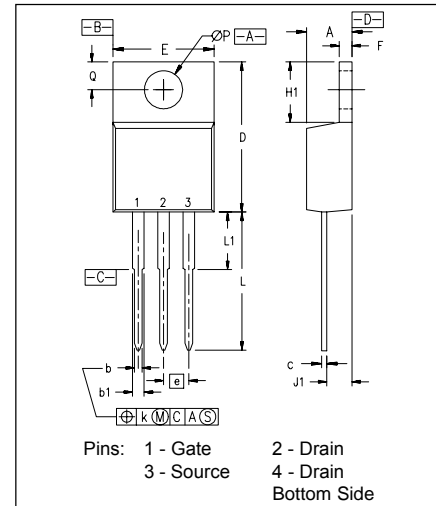
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	3N120	1200	V
		3N110	1100	V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ }\mu\text{A}$		2.5	V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$, $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		25 ∞A
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Note 1	3N120		4.5 Ω
		3N110		4.0 Ω

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	V _{DS} = 10 V; I _D = 0.5 • I _{D25} , Note 1	1.5	2.2		S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1050	1300	pF
C_{oss}			100	125	pF
C_{rss}			25	50	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 4.7 Ω (External),		17		ns
t_r			15		ns
t_{d(off)}			32		ns
t_f			18		ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		39		nC
Q_{gs}			9		nC
Q_{gd}			22		nC
R_{thJC}	(TO-220)			0.8	KW
R_{thCK}			0.25		KW

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
I_S	V _{GS} = 0 V			3	A
I_{SM}	Repetitive; pulse width limited by T _{JM}			12	A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5	V
t_{rr}	I _F = I _S , -di/dt = 100 A/∞s, V _R = 100 V		700		ns

Notes: 1. Pulse test, t ≤ 300 ∞s, duty cycle d ≤ 2 %

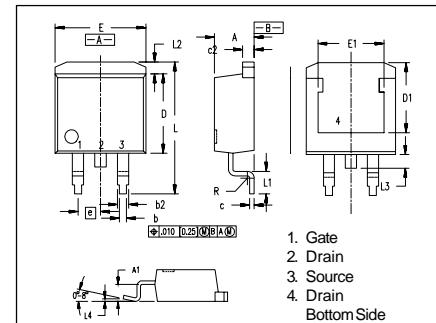
TO-220 (IXTP) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
∅P	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

TO-263 (IXTA) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

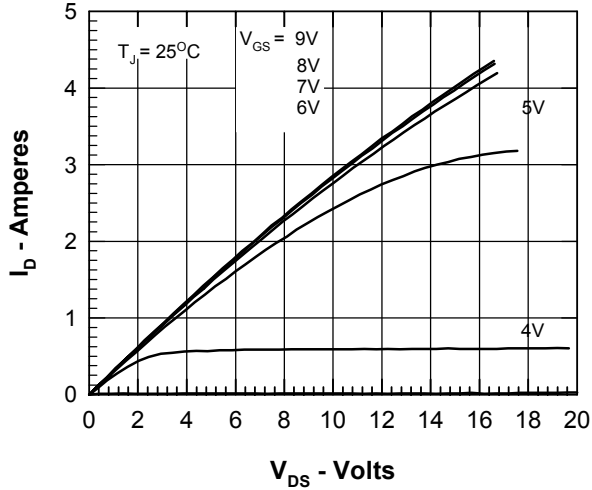


Fig.1 Output Characteristics @ $T_j = 25^\circ\text{C}$

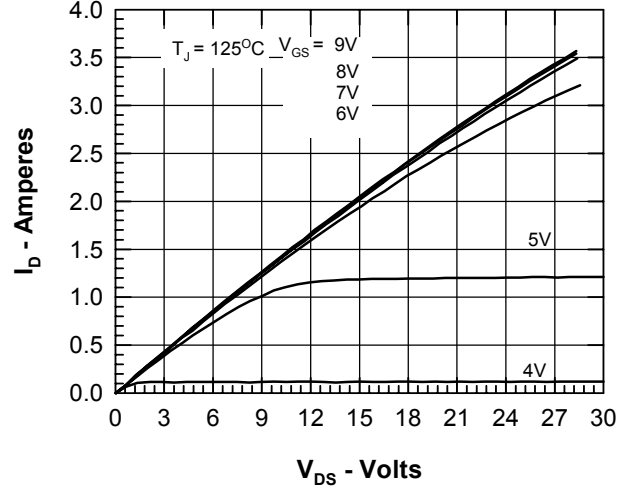


Fig. 2 Output Characteristics @ $T_j = 125^\circ\text{C}$

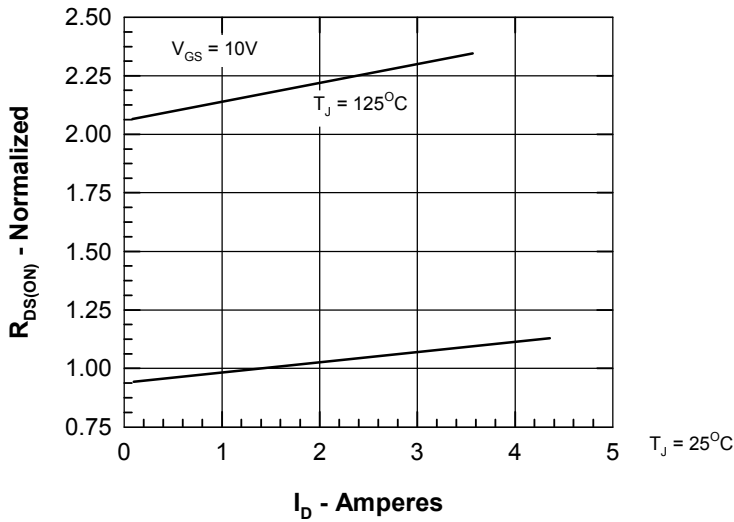


Fig. 3 $R_{DS(on)}$ vs. Drain Current

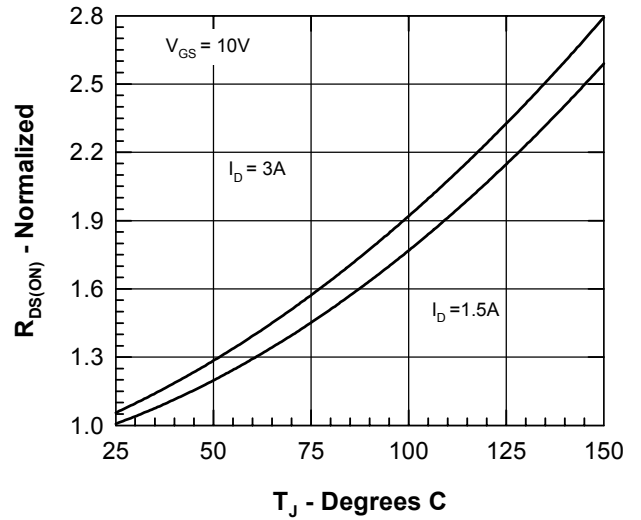


Fig. 4 Temperature Dependence of Drain to Source Resistance

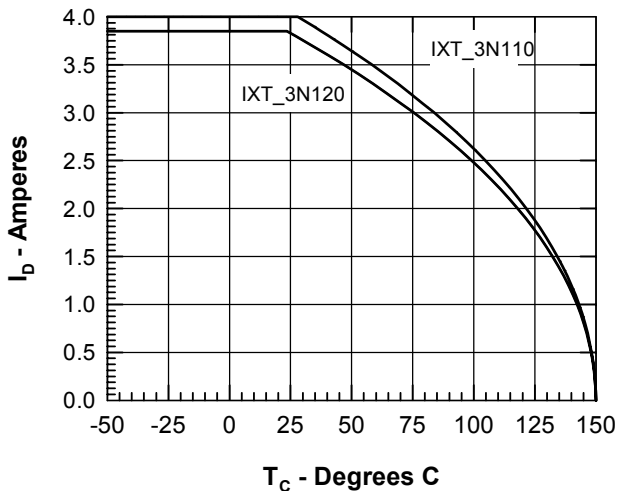


Fig. 5 Drain Current vs. Case Temperature

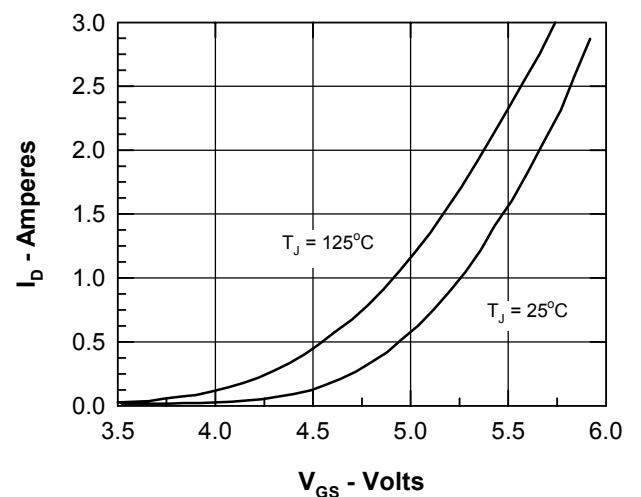


Fig. 6 Admittance Curves

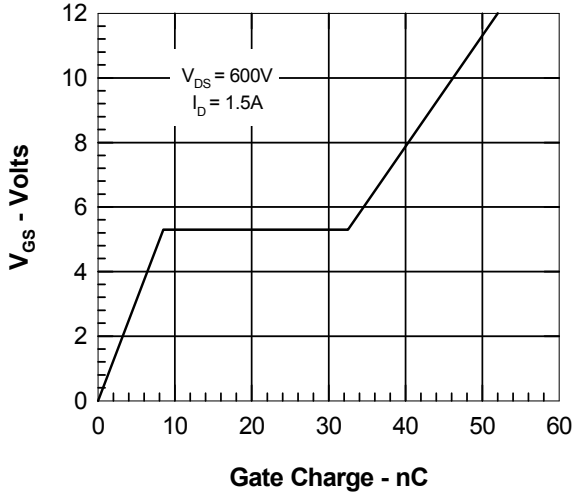


Fig. 7 Gate Charge Characteristic Curve

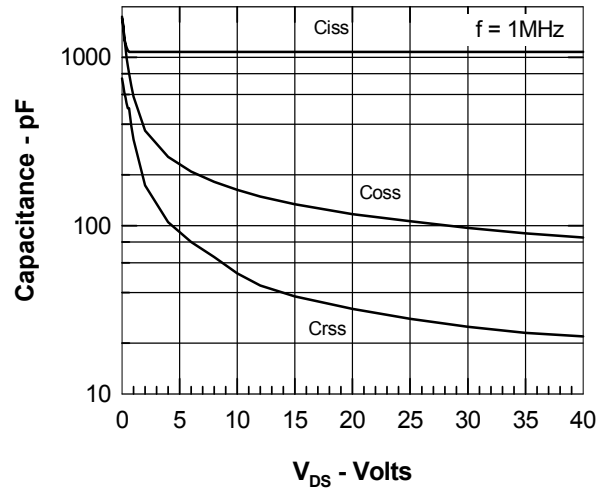


Fig. 8 Capacitance Curves

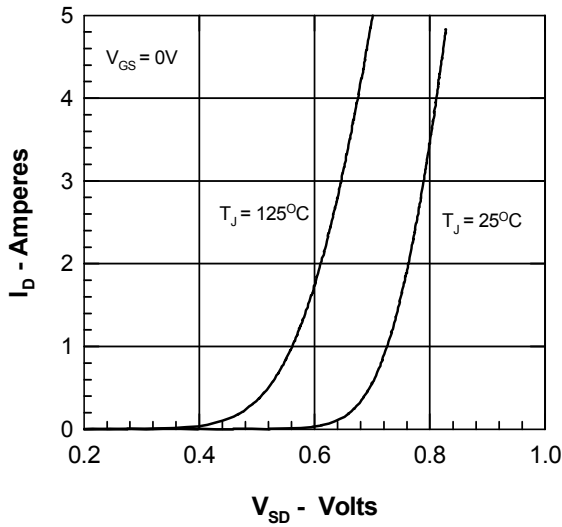


Fig. 9 Drain Current vs Drain to Source Voltage

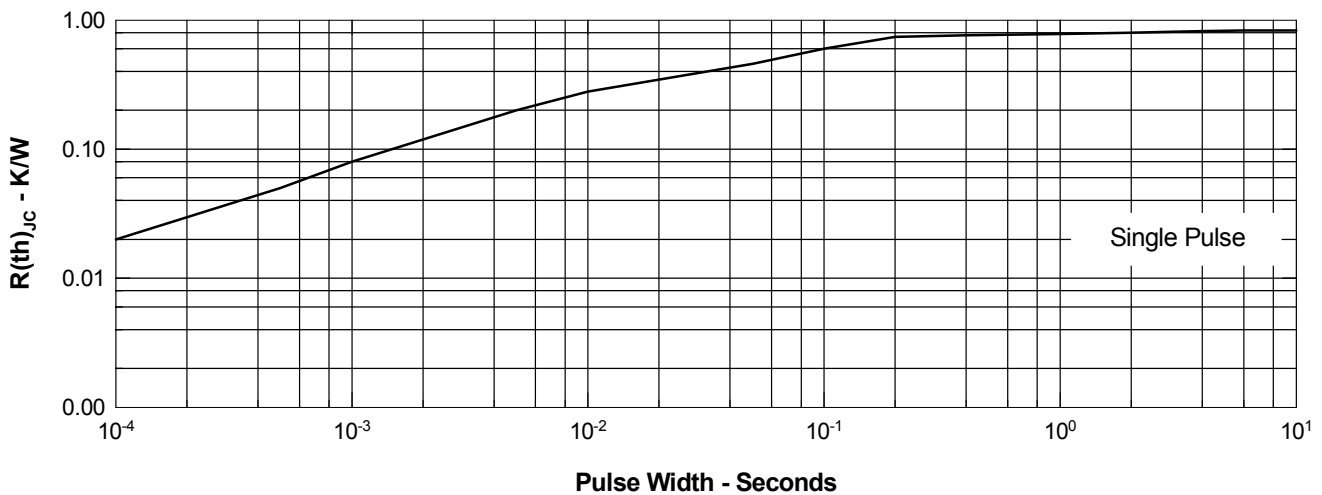


Fig.10 Transient Thermal Impedance

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4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	